



JOCT357X-M4 Series

Rev.A.1.0

DESCRIPTION:

The products are transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

MAIN FEATURES

- High isolation 3750 VRMS
- Operating temperature range -55°C to 110°C
- RoHS & REACH Compliance
- HBM: H3A; MM: M4; CDM:C3
- CQC approved
- VDE approved
- UL approved

ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I _F	50	mA
	Peak Forward Current	I _{FP}	1	A
	Reverse Voltage	V _R	6	V
	Power Dissipation	P _D	75	mW
Output	Collector-emitter Voltage	V _{CEO}	80	V
	Emitter-collector Voltage	V _{ECO}	7	V
	Collector Current	I _C	50	mA
	Power Dissipation	P		

Soldering Temperature	T_{sol}	260	
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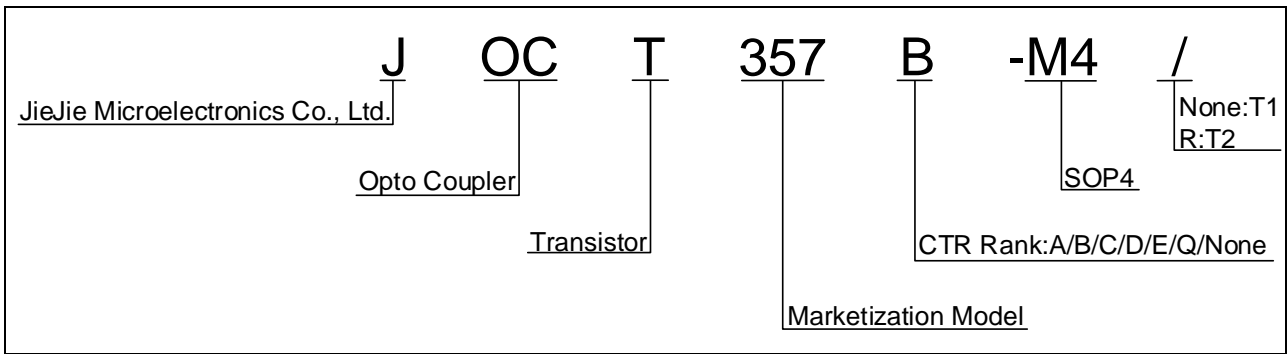
NOTE1 100 μ s pulse, 100Hz frequency

NOTE2 AC for 1minute, R.H.=40~60%

ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	$I_F=10mA$	-	1.2	1.5	V
	Reverse Current	I_R	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	C_t	$V=0,$ $f=1MHz$	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	$V_{CE}=20V,$ $I_F=0$	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	I				

ORDERING INFORMATION



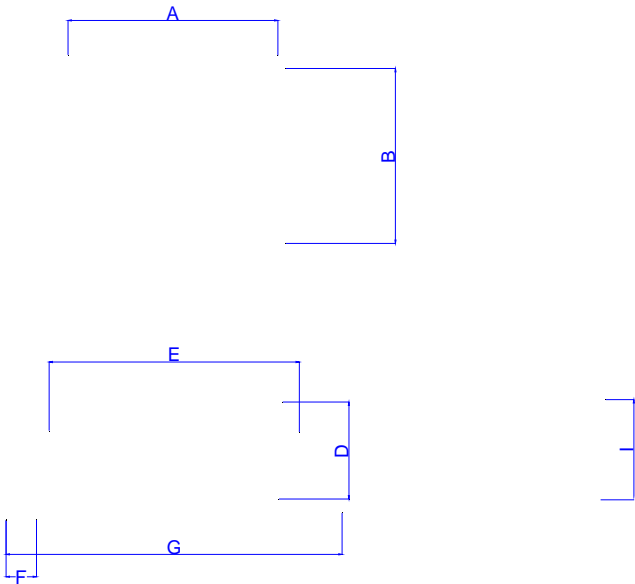
MARKING

Test Circuits

FIG.11: Test Circuits of Response Time

M M M M

Package Dimension (Unit: mm)





JOCT357X

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.